

TMR9003 TMR Linear Sensor

Features and Benefits

- Tunneling Magnetoresistance (TMR) Technology
- High Sensitivity (~30mV/V/Oe)
- Ultra-low Noise Spectral Density (750 pT/√Hz @1Hz)
- Very-low Power Consumption
- Excellent Thermal Stability
- Low Hysteresis
- Compatible with Wide Range of Supply Voltages
- No need for set/reset calibration

Applications

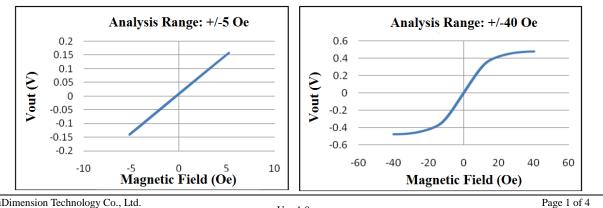
- Weak Magnetic Field Sensing
- Current Sensors
- Position and Displacement Sensing
- Biomedical Sensing
- Magnetic Communication

General Description

The TMR9003 linear sensor utilizes a unique push-pull Wheatstone bridge composed of four TMR sensor elements. The unique bridge design provides a high sensitivity differential output that is linearly proportional to a magnetic field applied parallel to the surface of the sensor package, and it provides superior temperature compensation of the output. The TMR9003 is assembled in a 6mm \times 5mm \times 1.5mm SOP8 package.

Transfer Curve

The following figure shows the response of the TMR9003 to an applied magnetic field in the range of ± 5 Oe and ± 40 Oe when the TMR9003 is biased at 1 V. The following specifications are calculated over an analysis range of ± 5 Oe.

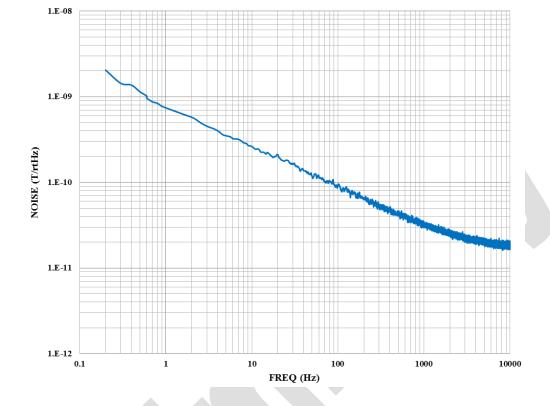




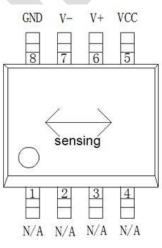
MDT TMR9003

Sensor Noise

The following figure illustrates the Power Spectral Density (PSD) of the TMR9003 self noise (N_i). The 1/f noise is approximately 750 pT/ \sqrt{Hz} @ 1Hz, and the white noise is approximately 20 pT/ \sqrt{Hz} @ 10kHz.







(SOP8 top view)

Pin No	Pin Name	Pin Function	
5	Vcc	Supply voltage	
6	V+	Analog Differential Output 1	
7	V-	Analog Differential Output 2	
8	GND	Ground	
1,2,3,4	N/A	Not connected	

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit	
Supply Voltage	V _{CC}	7	V	
Reverse Supply Voltage	V _{RCC}	7	V	
Magnetic Field	Н	5000	Oe ⁽¹⁾	
ESD Voltage	V _{ESD}	4000	V	
Operating Temperature	T_A	-40 ~ 125	°C	
Storage Temperature	Tstg	-50 ~ 150	°C	

Specification (V_{CC}=1.0V, T_A=25 °C, Differential Output)

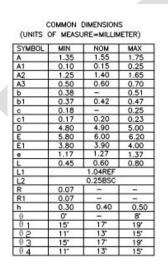
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Supply Voltage	V _{CC}	Normal Operation		1	7	V
Supply Current	I _{CC}	Output Open		20 ⁽²⁾		μA
Resistance	R			50		kOhm
Sensitivity	SEN	Fit±5 Oe		30		mV/V/Oe
Saturation Field	H _{sat}			±15		Oe
Non-Linearity	NONL	Fit±5 Oe		0.5		%FS
Offset Voltage	V _{offset}			10		mV/V
Hysteresis	Hys	Fit±5 Oe		0.1		Oe
Self Noise	Ni	@1Hz		750		pT/\sqrt{Hz}

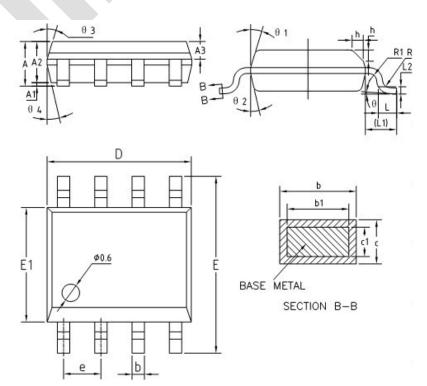
Note:

(1) 1 Oe (Oersted) = 1 Gauss in air = 0.1 millitesla = 79.8 A/m.

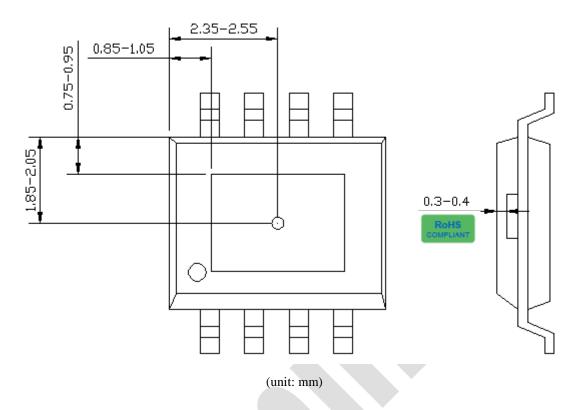
(2) $I_{CC} = V_{CC}/R$, Icc will vary under different R in practice and it can be customized accordingly.

Package information





Sensor Position



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